

The 2N322, 2N323, 2N324 are alloy junction PNP transistors intended for driver service in audio amplifiers. They are miniaturized versions of the 2N190 series of G.E. transistors. By control of transistor characteristics during manufacture, a specific power gain is provided for each type. Special processing techniques and the use of hermetic seals provides stability of these characteristics throughout life.

2N322, 2N323, 2N324

Outline Drawing No. 29

SPECIFICATIONS

ABSOLUTE MAXIMUM RATINGS:

Voltages		
Collector to Emitter	V_{CE}	-16 volts
Collector to Base	V_{CB}	-16 volts
Collector Current	I_C	50 ma

Power		
Collector Dissipation	P_{CM}	75 mw

Temperature		
Operating and Storage Range	T_A - T_{STG}	-65 to +85 °C

TYPICAL ELECTRICAL CHARACTERISTICS: (25°C)

D.C. Characteristics

	2N322	2N323	2N324
Base Current Gain ($I_C = 20$ ma; $V_{CE} = 1$ v) h_{FE}	48	80	95
Collector to Emitter Voltage ($R_{EB} = 10$ K, $I_C = .6$ ma)	V_{CE}	16	16
Collector Cutoff Current	I_{CO}	10	10
Max. Collector Cutoff Current	I_{CO}	16	16

Small Signal Characteristics

Frequency Cutoff ($V_{CE} = -5$ v; $I = 1$ ma)	f_{ab}	29	33	34
Collector Capacity ($V_{CE} = -5$ v; $I = 1$ ma)	C_{ob}	24	24	24
Noise Figure ($V_{CE} = -5$ v; $I = 1$ ma)	NF	10	10	10
Input Impedance ($V_{CE} = -5$ v; $I_E = 1$ ma)	h_{ie}	2200	2600	3300
Current Gain ($V_{CE} = -5$ v; $I_E = 1$ ma)	h_{ie}	70	84	112

Thermal Characteristics

Thermal Resistance Junction to Air		.33	.33	.33	°C/mw
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Performance Data Common Emitter

Power Gain Driver ($V_{CE} = 9$ v)	G_p	39	41	43	db
Power Output	P_o	1	1	1	mw

